

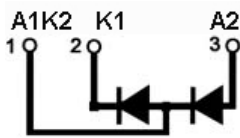
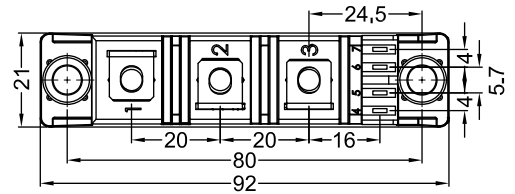
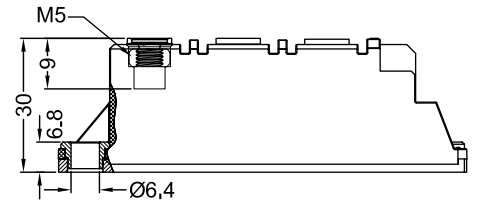
SDD60NXXB

Diode-Diode Modules

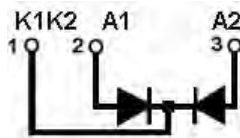


Type	V _{RSM} V	V _{RRM} V
SDD60N08B	900	800
SDD60N12B	1300	1200
SDD60N14B	1500	1400
SDD60N16B	1700	1600
SDD60N18B	1900	1800

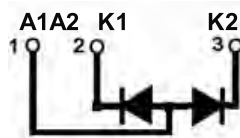
Holerance: ±0.5mm
Dimensions in mm (1mm=0.0394")



SDD



SDK



SDA

Symbol	Test Conditions	Maximum Ratings	Unit
I _{FRMS} I _{FAVM}	T _{VJ} =T _{VJM} T _C =100°C; 180° sine	100 60	A
I _{FSM}	T _{VJ} =45°C V _R =0 t=10ms (50Hz), sine t=8.3ms (60Hz), sine	1150 1300	A
	T _{VJ} =T _{VJM} V _R =0 t=10ms(50Hz), sine t=8.3ms(60Hz), sine	1000 1200	
∫i ² dt	T _{VJ} =45°C V _R =0 t=10ms (50Hz), sine t=8.3ms (60Hz), sine	6600 7000	A ² s
	T _{VJ} =T _{VJM} V _R =0 t=10ms(50Hz), sine t=8.3ms(60Hz), sine	5000 5950	
T _{VJ} T _{VJM} T _{stg}		-40...+150 150 -40...+125	°C
V _{ISOL}	50/60Hz, RMS I _{ISOL} ≤ 1mA t=1min t=1s	3000 3600	V~
M _d	Mounting torque (M5) Terminal connection torque (M5)	2.5-4/22-35 2.5-4/22-35	Nm/lb.in.
Weight	Typ.	105	g

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SDD60NXXB

Diode-Diode Modules

Symbol	Test Conditions	Characteristic Values	Unit
I_R	$T_{VJ}=T_{VJM}; V_R=V_{RRM}$	10	mA
V_F	$I_F=200A; T_{VJ}=25^{\circ}C$	1.50	V
V_{TO}	For power-loss calculations only	0.8	V
r_T	$T_{VJ}=T_{VJM}$	4.3	m Ω
Q_S	$T_{VJ}=125^{\circ}C; I_F=50A; -di/dt=0.64A/us$	90	μC
I_{RM}		11	A
R_{thJC}	per diode; DC current per module	0.40 0.20	K/W
R_{thJK}	per diode; DC current per module	0.60 0.30	K/W
d_s	Creepage distance on surface	12.7	mm
d_A	Strike distance through air	9.6	mm
a	Maximum allowable acceleration	50	m/s ²

FEATURES

- * International standard package
- * Copper base plate
- * Glass passivated chips
- * Isolation voltage 3600 V~
- * UL file NO.310749
- * RoHs compliant

APPLICATIONS

- * Supplies for DC power equipment
- * DC supply for PWM inverter
- * Field supply for DC motors
- * Battery DC power supplies

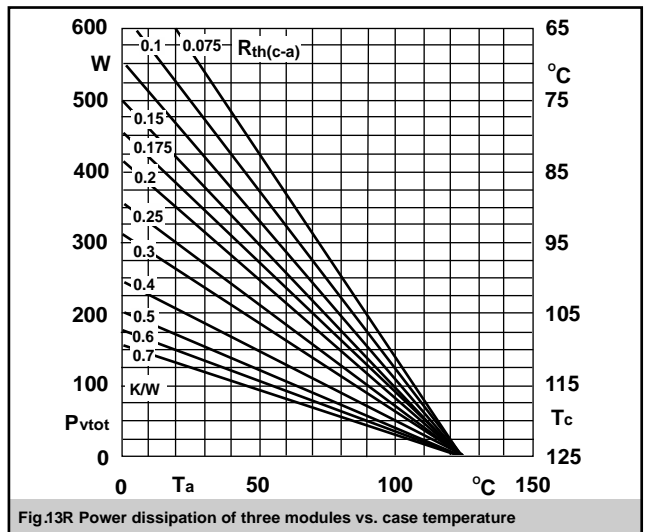
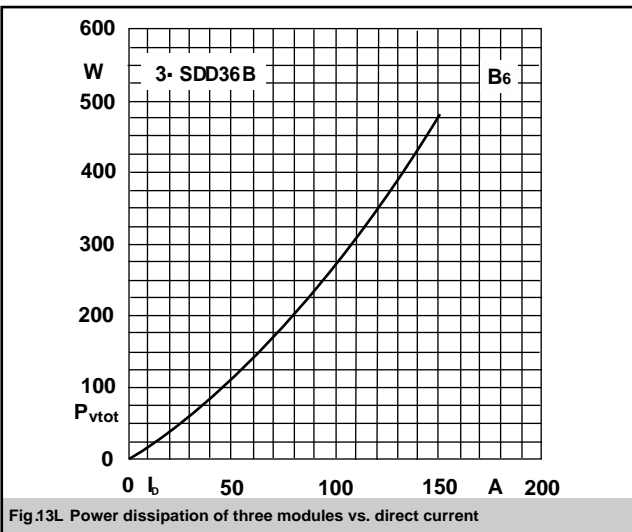
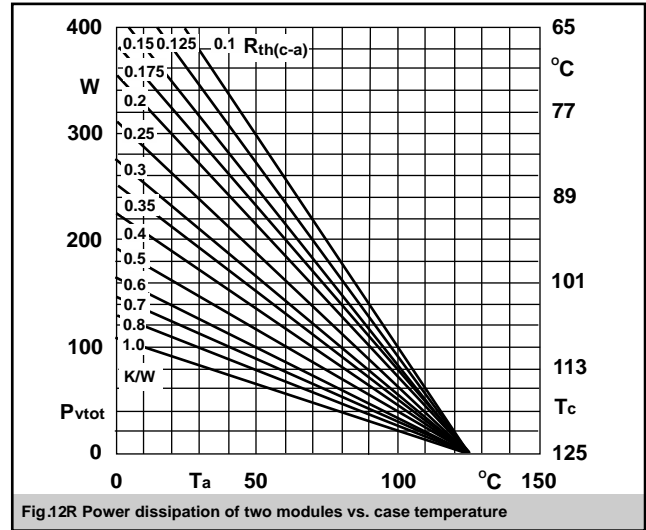
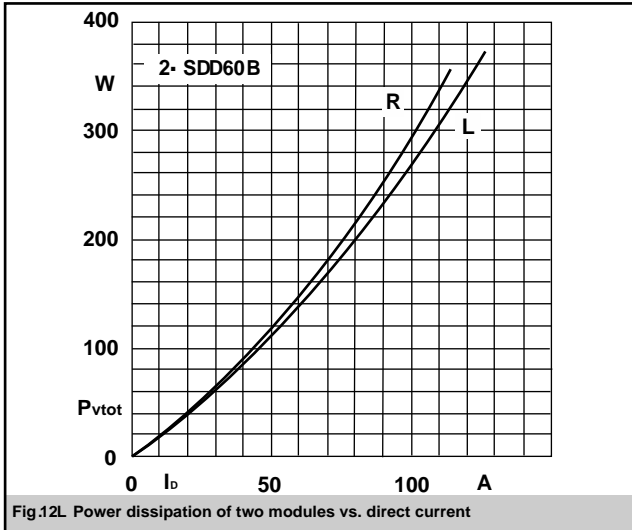
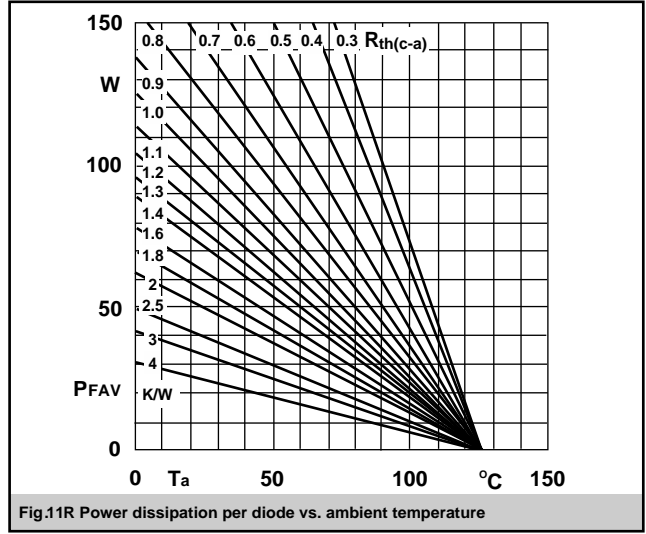
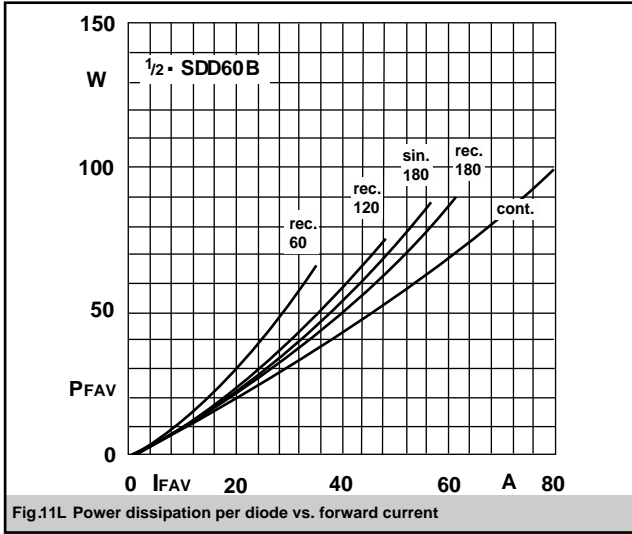
ADVANTAGES

- * Space and weight savings
- * Simple mounting
- * Improved temperature and power cycling
- * Reduced protection circuits

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SDD60NXXB

Diode-Diode Modules



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Diode-Diode Modules

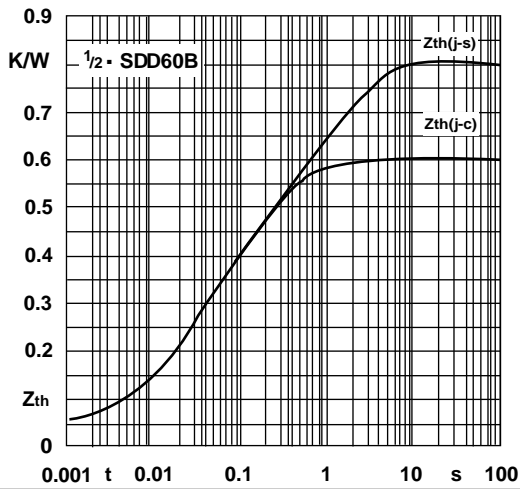


Fig.14 Transient thermal impedance vs. time

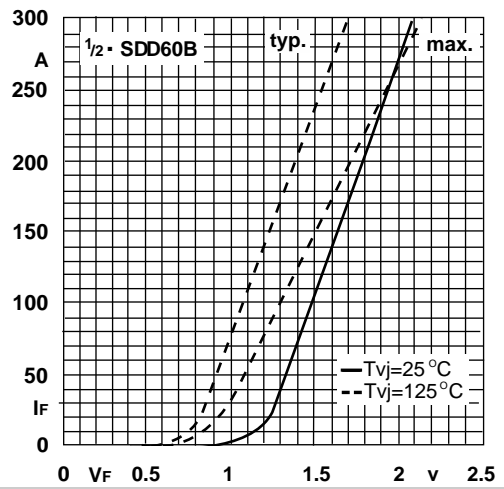


Fig.15 Forward characteristics

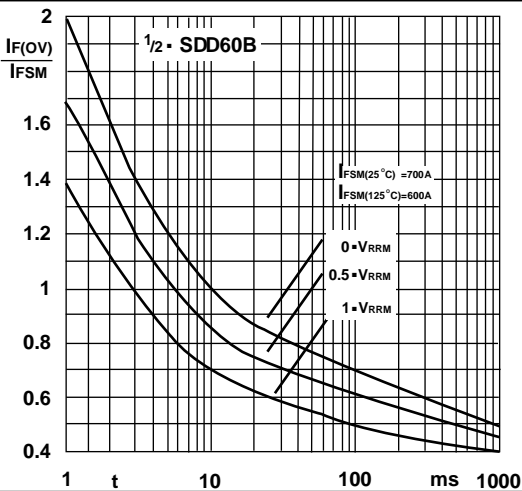


Fig.16 Surge overload current vs. time

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